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| First Named Inventor | Shun Chen | INFORMATION DISCLOSURE STATEMENT FORM PTO-1449 |
| Serial No. | 10/636,173 | |
| Filing Date | August 7, 2003 | |
| Group Art Unit | 2818 | |
| Examiner Name | Unknown PHAN | |
| Confirmation No. | 21057 2818 | |
| Attorney Docket No. | 400.234US01 | |
| Title: METHOD FOR PROGRAMMING AND ERASING AN NROM CELL | | Sheet 1 of 7 |

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| Confirmation No. | 2105 | |
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| Confirmation No. | 2105 | |
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